Electronic Structure and Transport Properties of LaNiO$_3$/LaAlO$_3$ Heterostructures$^1$ BENJAMIN GRAY, JIAN LIU, MIKHAIL KAREEV, University of Arkansas, ROSSITZA PENTCHEVA, Ludwig Maximilians University, DANIEL KHOMSKII, Universitaet zu Koeln, PHILIP RYAN, J.W. FREELAND, Advanced Photon Source, ANL, JAK CHAKHALIAN, University of Arkansas — In the bulk, the ground state of LaNiO$_3$ manifests itself as a correlated metal without magnetic ordering. Recent advances in fabrication of ultra-thin oxides allow for the synthesis of interface-controlled heterostructures with properties not attainable in their bulk counterparts. Towards this end, we fabricated high-quality LaNiO$_3$/LaAlO$_3$ superlattices epitaxially grown on SrTiO$_3$ and LaAlO$_3$ substrates by laser MBE. During the talk we present the experimental findings about effects of strain and proximity to the interface on the electronic and orbital structure of Ni, Al and O deduced from synchrotron soft x-ray spectroscopy, XRD, and bulk electric and thermal measurements.

$^1$This work was supported by DOD-ARO under Contract No. 0402-17291 and NSF under Contract No. DMR-0747808.